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# Power Matters.

Home ▶ 2N911 (#18699)

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#### ▶ Product Directory

**Products** 

- Froduct DirectoryApplications Directory
- ▶ Parametric Search

## Overview Diagrams

Electrical Rating	Symbol	Min	Тур	Max	Unit
Bandwidth	BW	50.00			MHz
Collector to Emitter Saturation Voltage	V <sub>CE(sat)</sub>			1.00	V
DC Current Gain	HFE	35.00		140.00	

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V <sub>BR(CBO)</sub>			100.00	V
Collector-Emitter Voltage (Base Open)	V <sub>CEO</sub>			60.00	V
Emitter-Base Voltage (Collector Open)	V <sub>EBO</sub>			7.00	V
Power Dissipation, Total	P <sub>T</sub>			0.50	W

This part can be found in the following product categories:

- → Discretes → Transistors → BJT( BiPolar Junction Transistor) → PNP Transistor
- Non-Radiation Hardened Devices ▶ Transistors ▶ BJT( BiPolar Junction Transistor) ▶ NPN Transistor

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